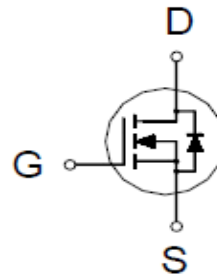


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PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
30V	7.8m Ω @ $V_{GS} = 10V$	36A



ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current ⁴	$T_C = 25\text{ }^{\circ}\text{C}$	I_D	36	A
	$T_C = 100\text{ }^{\circ}\text{C}$		23	
Pulsed Drain Current ¹		I_{DM}	100	
Continuous Drain Current	$T_A = 25\text{ }^{\circ}\text{C}$	I_D	14	
	$T_A = 70\text{ }^{\circ}\text{C}$		11	
Avalanche Current		I_{AS}	22	
Avalanche Energy	$L = 0.1\text{mH}$	E_{AS}	24	mJ
Power Dissipation	$T_C = 25\text{ }^{\circ}\text{C}$	P_D	20	W
	$T_C = 100\text{ }^{\circ}\text{C}$		8.3	
Power Dissipation ³	$T_A = 25\text{ }^{\circ}\text{C}$		3.1	
	$T_A = 70\text{ }^{\circ}\text{C}$		2	
Operating Junction & Storage Temperature Range		T_J, T_{stg}	-55 to 150	$^{\circ}\text{C}$

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THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE		SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient ²	$t \leq 10s$	$R_{\theta JA}$		40	°C / W
Junction-to-Ambient ²	Steady-State	$R_{\theta JA}$		68	
Junction-to-Case	Steady-State	$R_{\theta JC}$		6	

¹Pulse width limited by maximum junction temperature.

²The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.

³The Power dissipation is based on $R_{\theta JA}$ $t \leq 10s$ value.

⁴Package limitation current is 13A.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNITS
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	30			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.3	1.75	2.3	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 24V, V_{GS} = 0V$			1	μA
		$V_{DS} = 20V, V_{GS} = 0V, T_J = 55^\circ C$			10	
Drain-Source On-State Resistance ¹	$R_{DS(ON)}$	$V_{GS} = 4.5V, I_D = 13A$		7.3	11	m Ω
		$V_{GS} = 10V, I_D = 13A$		5.5	7.8	
Forward Transconductance ¹	g_{fs}	$V_{DS} = 5V, I_D = 13A$		47		S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 15V, f = 1MHz$		864		pF
Output Capacitance	C_{oss}			146		
Reverse Transfer Capacitance	C_{rss}			106		
Gate Resistance	R_g	$V_{GS} = 0V, V_{DS} = 0V, f = 1MHz$		1		Ω
Total Gate Charge ²	$Q_g(V_{GS}=10V)$	$V_{DS} = 15V, V_{GS} = 10V, I_D = 13A$		18		nC
	$Q_g(V_{GS}=4.5V)$			10		
Gate-Source Charge ²	Q_{gs}			1.8		
Gate-Drain Charge ²	Q_{gd}			5.2		
Turn-On Delay Time ²	$t_{d(on)}$	$V_{DS} = 15V, I_D \cong 13A, V_{GS} = 10V, R_{GEN} = 6\Omega$		17		nS
Rise Time ²	t_r			25		
Turn-Off Delay Time ²	$t_{d(off)}$			30		
Fall Time ²	t_f			18		

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SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ($T_J = 25\text{ }^{\circ}\text{C}$)

Continuous Current ³	I_S			16	A
Forward Voltage ¹	V_{SD}	$I_F = 13\text{A}, V_{GS} = 0\text{V}$		1.2	V
Reverse Recovery Time	t_{rr}	$I_F = 13\text{A}, dI_F/dt = 100\text{A} / \mu\text{S}$		7.5	nS
Reverse Recovery Charge	Q_{rr}			1.5	nC

¹Pulse test : Pulse Width $\leq 300\text{ }\mu\text{sec}$, Duty Cycle $\leq 2\%$.

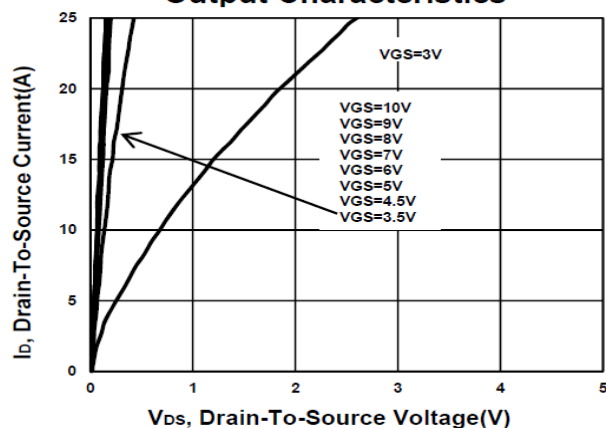
²Independent of operating temperature.

³Package limitation current is 13A.

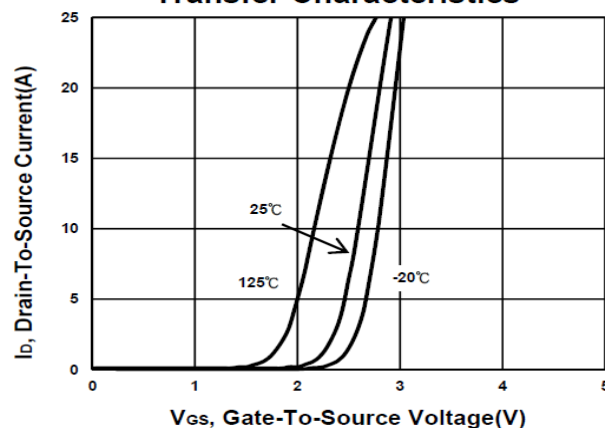
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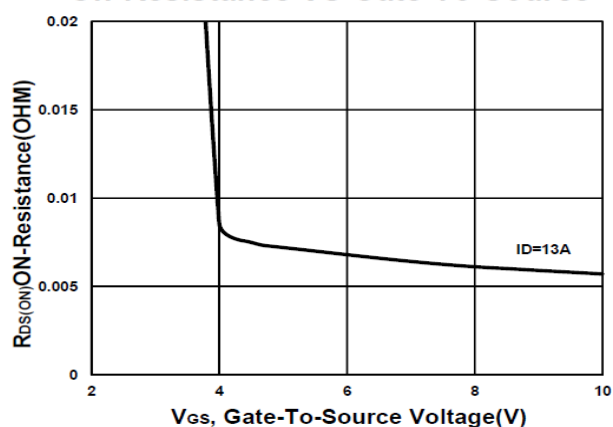
Output Characteristics



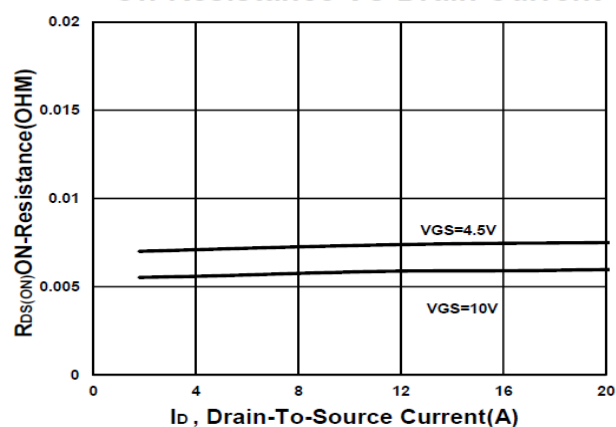
Transfer Characteristics



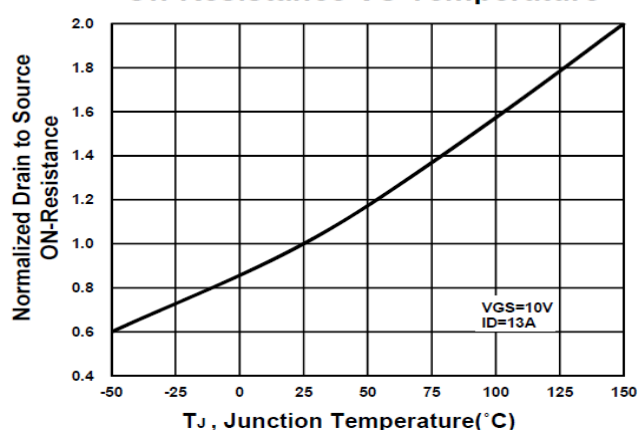
On-Resistance VS Gate-To-Source



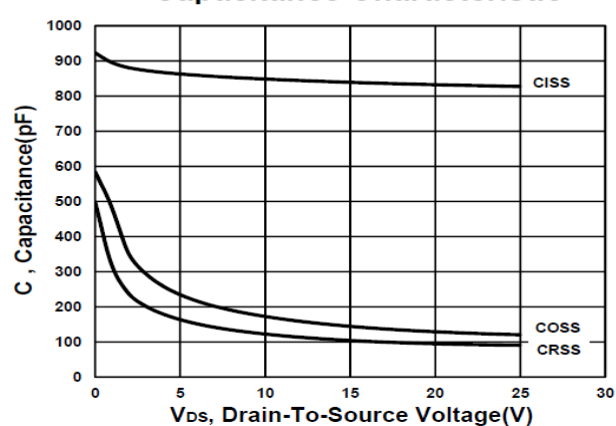
On-Resistance VS Drain Current



On-Resistance VS Temperature



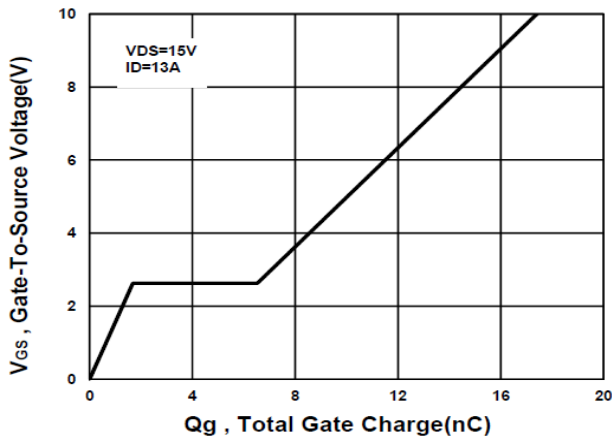
Capacitance Characteristic



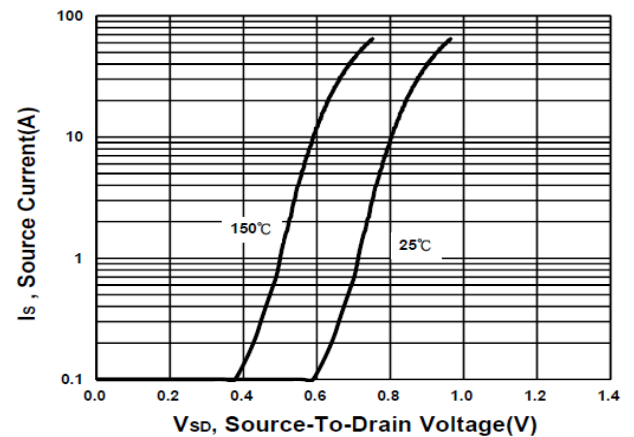
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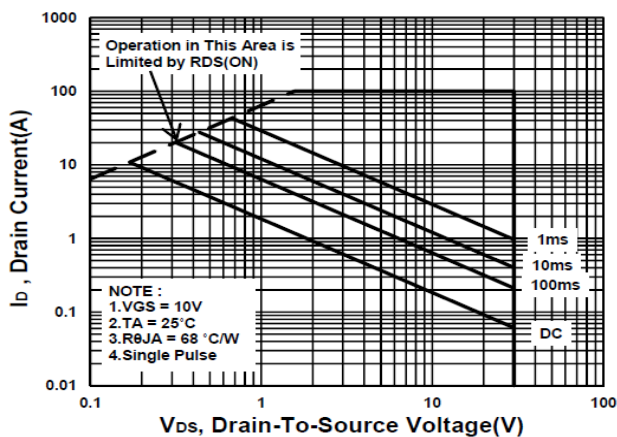
Gate charge Characteristics



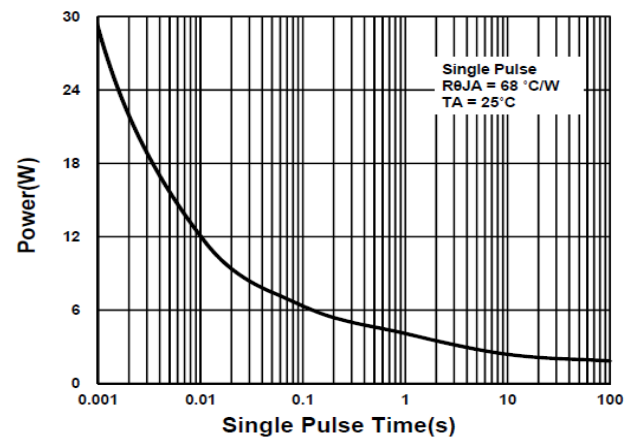
Source-Drain Diode Forward Voltage



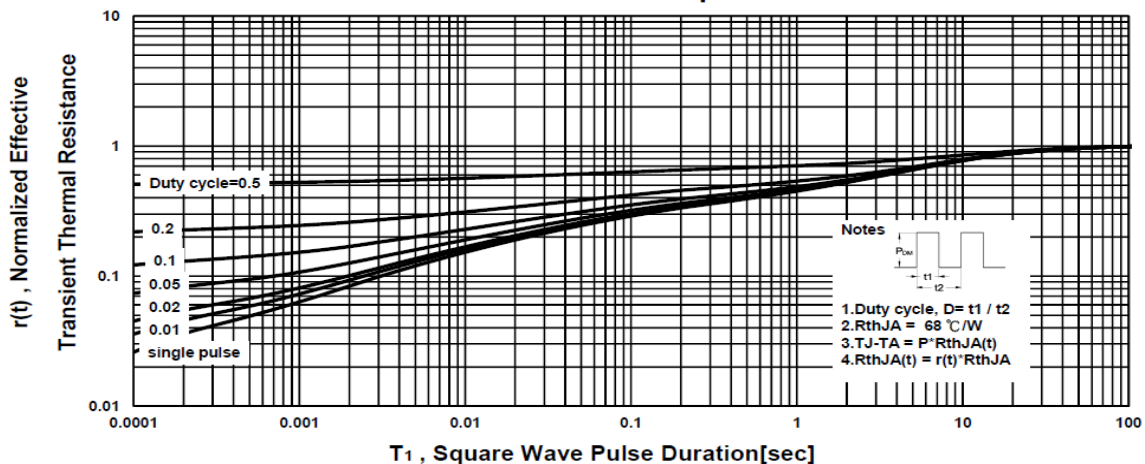
Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve



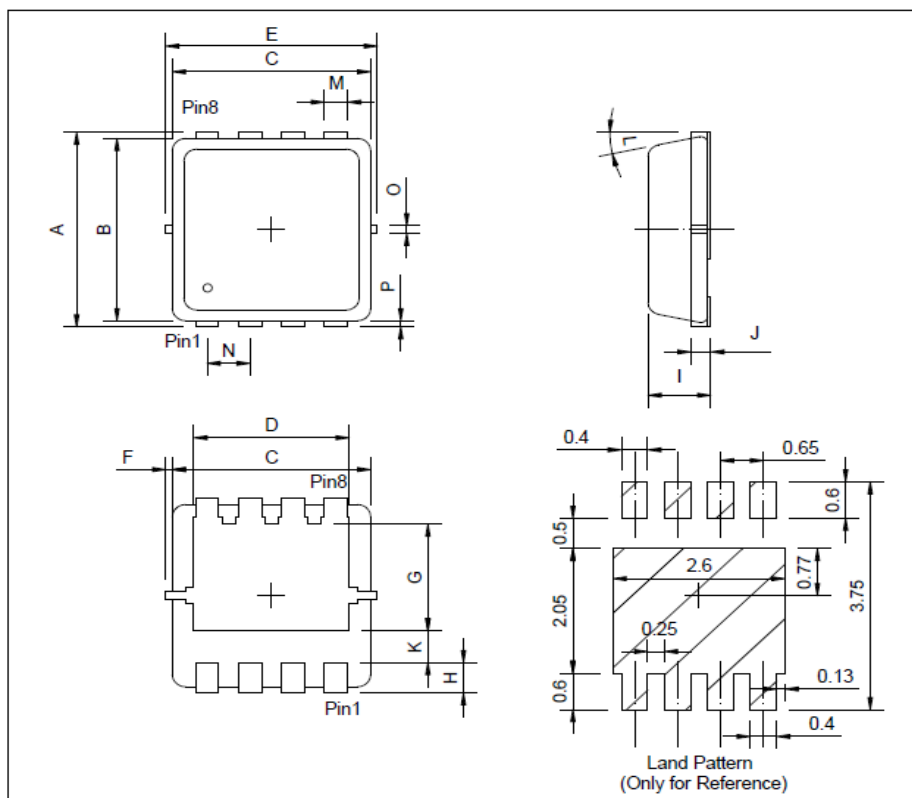
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Package Dimension

PDFN 3x3P MECHANICAL DATA

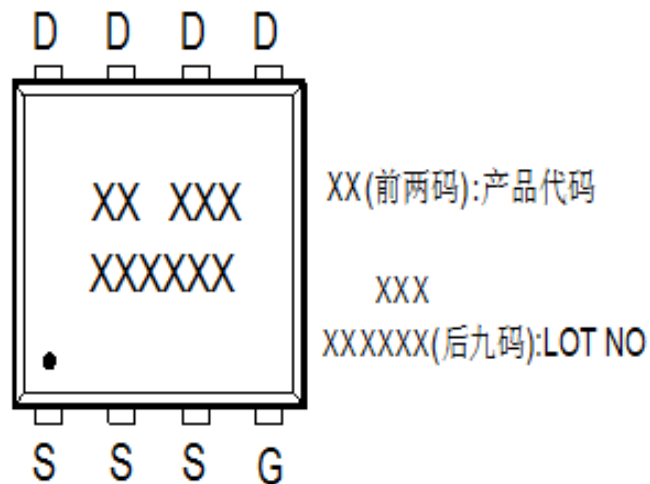
Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	3	3.3	3.6	I	0.65	0.8	0.9
B	2.88	3	3.2	J	0.1	0.15	0.25
C	2.9	3	3.25	K	0.59		
D	2.29	2.45	2.69	L	0°	10°	12°
E	3	3.3	3.6	M	0.14	0.3	0.4
F	0	0.1	0.2	N	0.55	0.65	0.75
G	1.35	1.75	2.2	O		0.2	
H	0.15	0.3	0.55	P	0		0.2



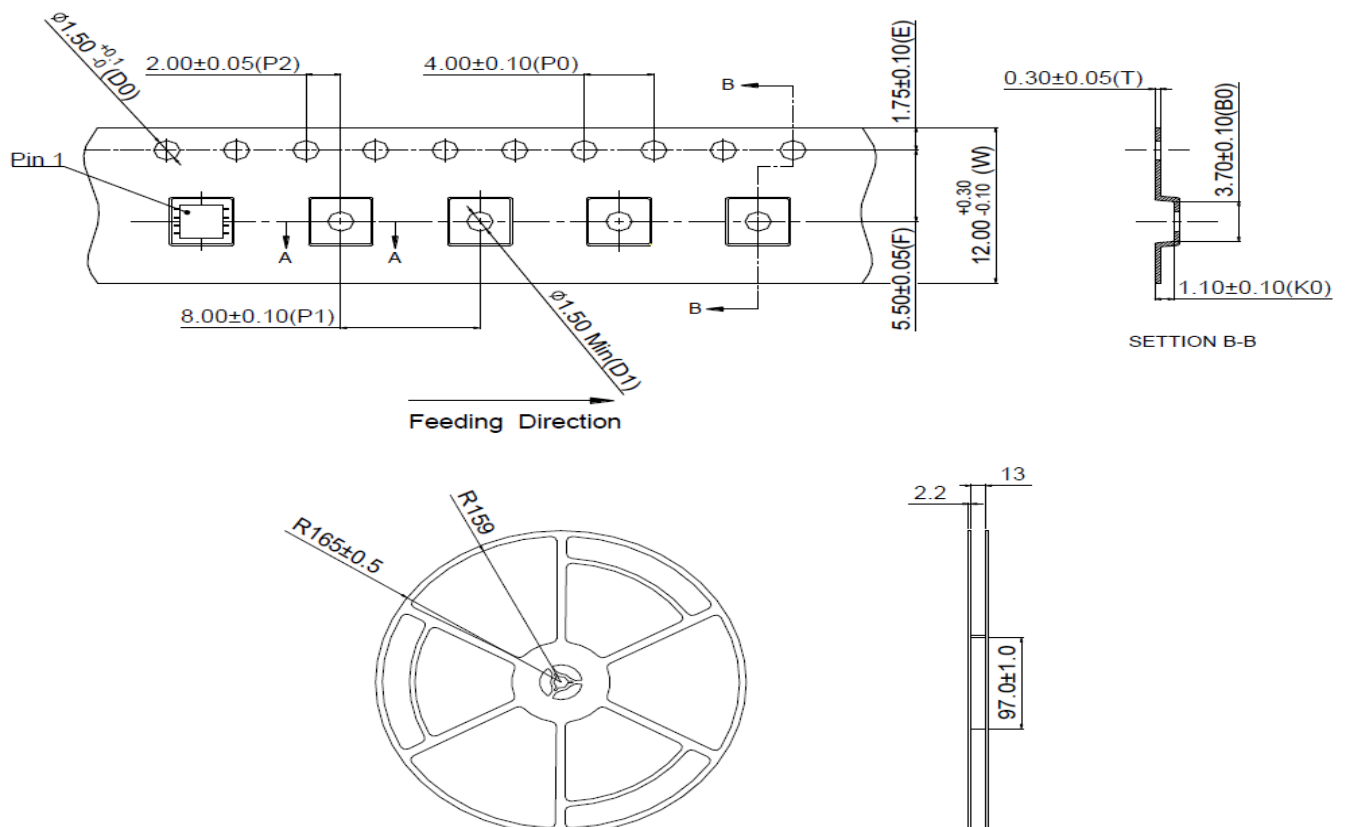
PE6H6BA

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A. Marking Information(此产品代码为: M1)



B. Tape&Reel Information:5000pcs/Reel

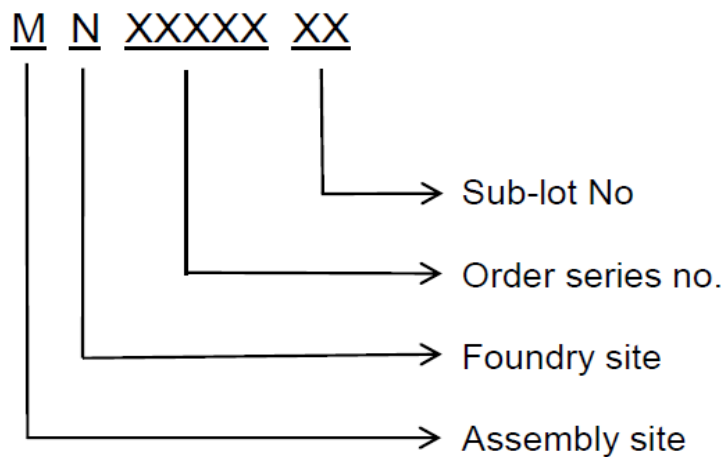


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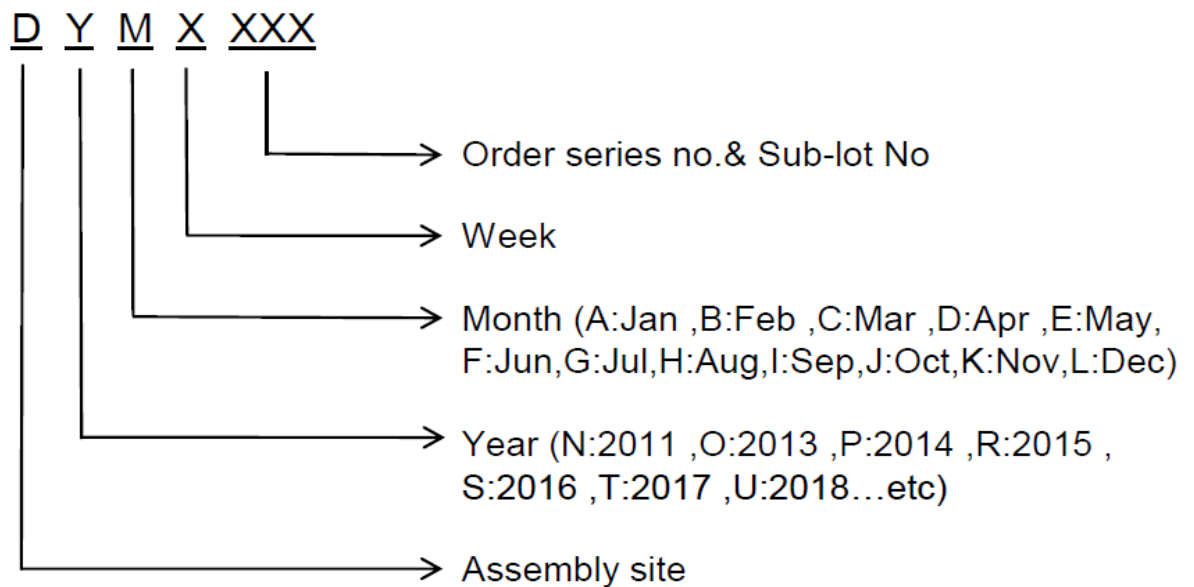
N-Channel Enhancement Mode MOSFET

C. Lot No.&Date Code rule

1.Lot No.



2.Date Code



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D.Label rule

标签内容(Label content)



1	Label Size	30 * 90 mm
2	Font style	Times New Roman or Arial (或可区分英文"0"和数字"0", "G"和"Q"的字型即可)
3	U-NIKC	Height: 4 mm
4	Package	Height: 2 mm
5	Date	Height: 2 mm Shipping date: YYYY/MM/DD, ex. 2008/09/12
6	Device	Height: 3 mm (Max: 16 Digit)
7	Lot	Height: 3 mm (Max: 9 Digit) Sub lot
8	D/C	Height: 3 mm (Max: 7 Digit)
9	QTY	Height: 3 mm (Max: 6 Digit) Thousand mark is no needed
10	RoHS label	 long axis: 12 mm minor axis: 6 mm bottom color: White Font color: Black Font style: Arial
11	Halogen Free label	 Diameter: 10 mm bottom color: Green Font color: Black Font style: Arial
12	Scan information	Device / Lot / D/C / QTY , Insert " / " between every parts. for example: P3055LDG/G12345601/GGG2301/2000 DPI (Dots per inch): Over 300 dpi Code : Code 128 Height: 6 mm at least